Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	9077	438/761,636,689,702,780,763, 778,931,952,740,355,395.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 13:50
L2	17	1 and ((silicon Si) with (carbon C) with (noble He Ar Ne Kr) with plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 13:51
L3	4	2 and (anti adj reflect$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 13:51
L4	8	2 and (SiC (silicon adj carbide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 13:52
L5	312	((silicon Si) with (carbon C) with (noble He Ar Ne Kr) with plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 13:53
L6	104	((silicon Si) with (carbon C) with (noble He Ar Ne Kr) with plasma) and (SiC (silicon adj carbide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 14:03
L7	14	6 and (anti adj reflect$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 13:55
L8	39	6 and (photoresist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 13:54
L9	12	6 and (anti adj reflect$4) and (photoresist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 13:55

| L10 | . | 4 | ((silicon Si) with (carbon C) with (noble He Ar Ne Kr) with plasma) and ((SiC (silicon adj carbide)) with (first near3 dielectric) with (second near3 dielectric)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/29 14:06 |